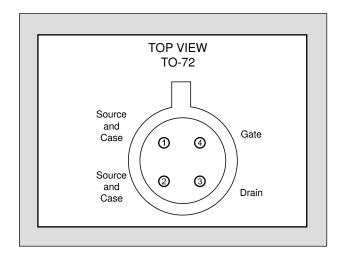


### Twenty-Five Years Of Quality Through Innovation

FEATURES					
HIGH INPUT IMPEDANCE	$r_{Gs}$ = 100G $\Omega$				
HIGH TRANSCONDUCTANCE	$Y_{FS} = 30,000 \mu S$				
ABSOLUTE MAXIMUM RATINGS <sup>1</sup>					
@ 25 ℃ (unless otherwise stated)					
Maximum Temperatures					
Storage Temperature	-55 to +150 ℃				
Operating Junction Temperature	-55 to +125 ℃				
Maximum Power Dissipation					
Continuous Power Dissipation @ +25 ℃	200mW				
Maximum Currents					
Drain Current	$I_D = 25mA$				
Maximum Voltages					
Drain to Source <sup>1</sup>	$V_{DSO} = 20V$				
Gate to Source	$V_{GSS} = 20V$				

## **LS320**

# HIGH INPUT IMPEDANCE BIFET AMPLIFIER

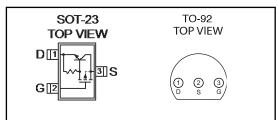


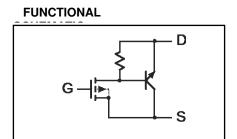
### ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
$V_{DS}$	Drain to Source Voltage	-20			V	$I_{DS} = 100 \mu A, V_{GS} = 0 V$
$V_{GS}$	Gate to Source Voltage	-7	-10	-12	V	$I_{DS} = 10 \text{mA}, \ V_{DS} = -10 \text{V}^{2,3}$
<b>g</b> fs	Common Source Forward Transconductance	30,000			μS	$I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}, f = 1 \text{kHz}$
goss	Common Source Output Conductance		300		μS	$I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}, f = 1 \text{kHz}$
r <sub>Gs</sub>	Gate to Source Input Resistance	100			GΩ	$V_{GS}$ = 0 to 20V, $T_J$ to 125 $^{\circ}$ C
C <sub>ISS</sub>	Input Capacitance		8		рF	$I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}$
C <sub>RSS</sub>	Reverse Transfer Capacitance		1.5		рF	$I_{DS} = 10 \text{mA}, V_{DS} = -10 \text{V}$
e <sub>n</sub>	Noise Voltage		25		μV	$I_{DS} = 10 \text{mA}, V_{DS} = 10 \text{V}$ BW = 50 to 15kHz

All limits are absolute numbers. Negative signs indicate electrical polarity.

#### **PACKAGE OPTIONS**





- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- 2. The gate to source voltage must never exceed 100V, t < 10ms.
- 3. Additional screening available

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Linear Integrated Systems (LIS) is a 25-year-old, third-generation precision semiconductor company providing high-quality discrete components. Expertise brought to LIS is based on processes and products developed at Amelco, Union Carbide, Intersil and Micro Power Systems by company President John H. Hall. Hall, a protégé of Silicon Valley legend Dr. Jean Hoerni, was the director of IC Development at Union Carbide, co-founder and vice president of R&D at Intersil, and founder/president of Micro Power Systems.